

# Kingtronics®

# BT134-600E

## SENSITIVE GATE TRIAC

Blocking voltage - 600 Volts On-state RMS current - 4.0 Ampere

### FEATURES

- ◆ Ultra low gate trigger current
- ◆ Low cost package

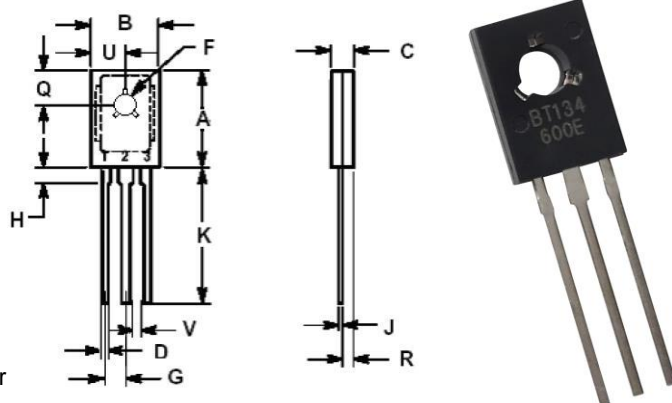
### APPLICATIONS

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

### DESCRIPTION

Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bi-directional switching and phase control applications, where high sensitivity is required in all four quadrants.

### SOT-126



DIM	Inches			Millimeters		
	Min	Type	Max	Min	Type	Max
A	0.419	-	0.429	10.650	-	10.890
B	0.284	-	0.312	7.220	-	7.920
C	0.091	0.100	0.109	2.300	2.540	2.760
K	0.520	-	0.598	13.200	-	15.200
D	0.025	0.029	0.031	0.640	0.730	0.800
J	0.011	-	0.020	0.280	-	0.520
G	0.087	0.091	0.094	2.200	2.300	2.400
V	0.040	-	-	1.020	-	-
F	0.115	0.122	0.130	2.930	3.100	3.300
U	0.142	-	0.157	3.600	-	4.000
Q	0.151	-	0.163	3.830	-	4.130
H	0.071	0.102	0.114	1.800	2.600	2.900
R	0.045	-	0.065	1.150	-	1.650

### PINNING INFORMATION

PIN	Description	Simplified outline	Symbol
1	main terminal 1(T1)		
2	main terminal 2(T2)		
3	Gate(G)		
tab	main terminal		

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX	UNIT
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltages	600	V
$I_{T(RMS)}$	RMS on-state current	4	A
$I_{TSM}$	Non-repetitive peak on-state current	10	A

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction to Case	in free air	-	-	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	in free air	-	-	75	°C/W
$T_L$	Maximum Lead Temperature for Soldering Purposes for 10 Seconds	in free air	-	-	260	°C

**Kingtronics® International Company**

**Kingtronics**®**BT134-600E****SENSITIVE GATE TRIAC****Blocking voltage - 600 Volts On-state RMS current - 4.0 Ampere****LIMITING VALUE**

Limiting values in accordance with the Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltages		-	600	V
$I_{T(RMS)}$	RMS on-state current	Full Cycle Sine Wave 50 to 60 Hz (TC = 85°C)	-	4	A
$I_{TSM}$	Non-repetitive peak on -state current	One Full Cycle, Sine Wave 60 Hz (TC = 110°C)	-	40	A
$I^2t$	$I^2t$ for fusing	t = 8.3 ms	-	3.7	A <sup>2</sup> s
$V_{GM}$	Peak gate voltage	Pulse Width ≤ 1.0us, TC = 85°C	-	5	V
$P_{GM}$	Peak gate power	Pulse Width ≤ 1.0us, TC = 85°C	-	10	W
$P_{G(AV)}$	Average gate power	Pulse Width ≤ 1.0us, TC = 85°C	-	0.5	W
$T_{stg}$	Storage temperature		-40	150	°C
$T_j$	Operating junction temperature		-40	110	°C

**CHARACTERISTICS** $T_J = 25^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
<b>Static characteristics</b>						
$I_{GT}$	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ T2+ G+	-	3	10	mA
		T2+ G-	-	3	10	mA
		T2- G-	-	3	10	mA
		T2- G+	-	8	25	mA
$I_L$	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ T2+ G+	-	1.5	15	mA
		T2+ G-	-	5	20	mA
		T2- G-	-	1.0	15	mA
		T2- G+	-	3.0	20	mA
$I_H$	Holding current	Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current ≤ 1 Adc $T_J = 25^\circ\text{C}$	-	-	15	mA
		$T_J = -40^\circ\text{C}$	-	-	30	mA
$V_{TM}$	On-state voltage	$I_{TM} = \pm 6\text{ A Peak}$	-	1.4	2	V
$V_{GT}$	Gate trigger voltage (Continuous dc)	Main Terminal Voltage = 12 Vdc, $R_L = 100\text{ Ohms}$ , $T_J = -40^\circ\text{C}$ All Quadrants	-	1.4	2.5	V
$V_{GD}$	Gate Non-Trigger Voltage	Main Terminal Voltage = 12 Vdc, $R_L = 100\text{ Ohms}$ , $T_J = 110^\circ\text{C}$ All Quadrants	0.2	-	-	V

**Dynamic Characteristics**

$dv/dt(c)$	Critical rate of rise of off-state voltage	$V_{DRM}$ , $T_J = 85^\circ\text{C}$ , Gate Open, $I_{TM} = 5.7\text{ A}$ , Exponential Waveform, Commutating $di/dt = 2.0\text{ A/ms}$	-	5	-	V/ $\mu\text{s}$
tgt	Gate controlled turn-on time	$I_{TM} = 14\text{ Adc}$ , $I_{GT} = 100\text{ mA dc}$	-	1.5	-	$\mu\text{s}$

**Kingtronics**® International Company

## RATINGS AND CHARACTERISTIC CURVES BT134-600E

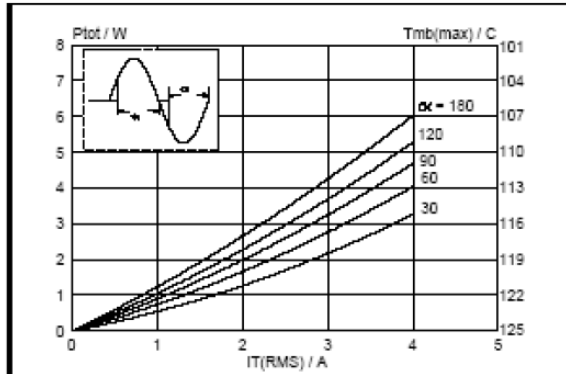


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

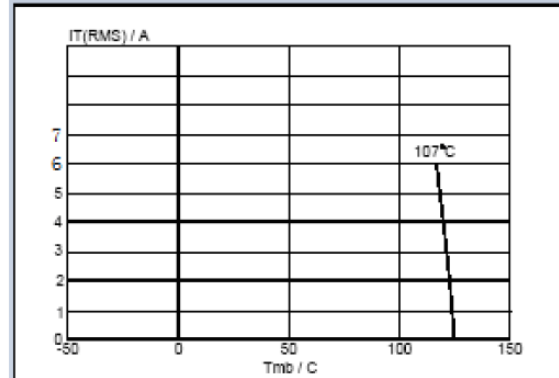


Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

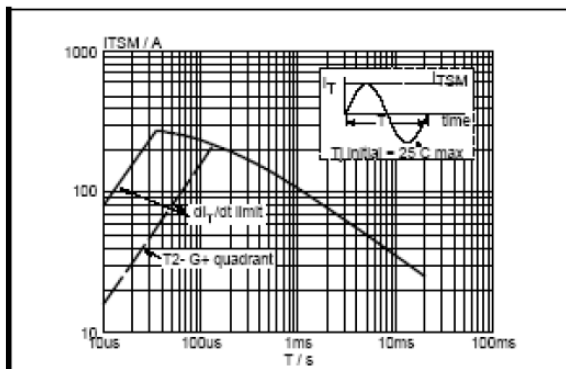


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20ms$ .

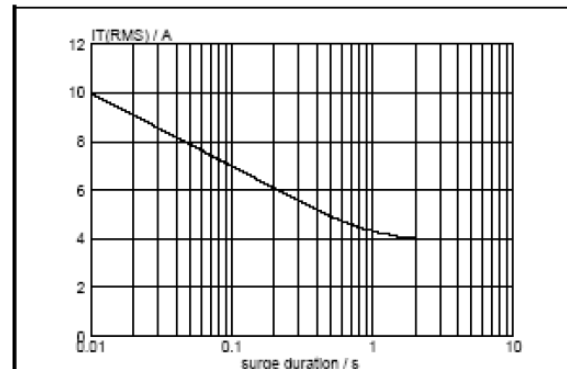


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50 Hz$ ;  $T_{mb} \leq 107^\circ C$ .

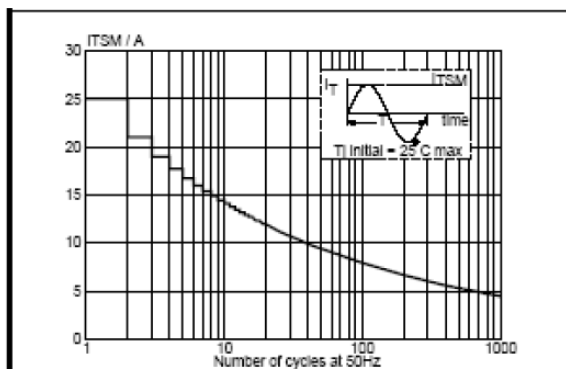


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50 Hz$ .

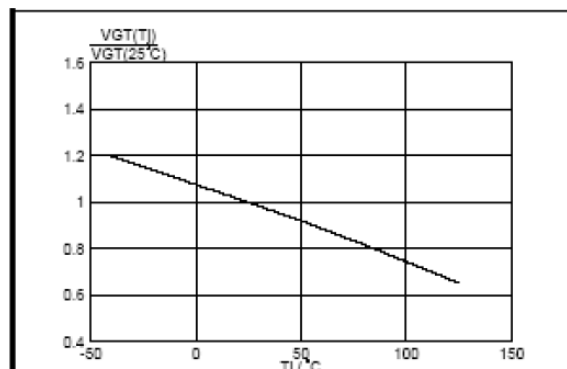
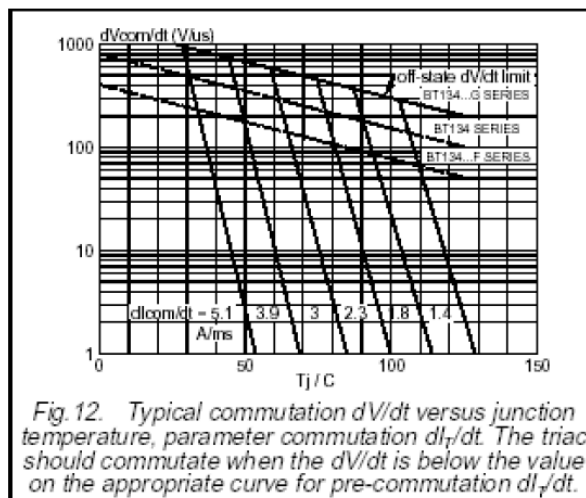
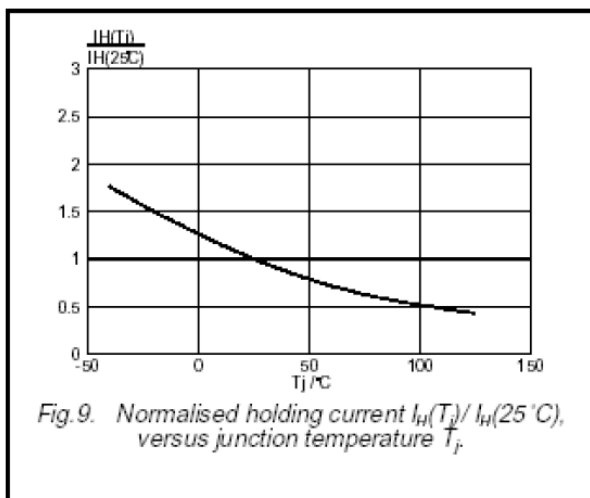
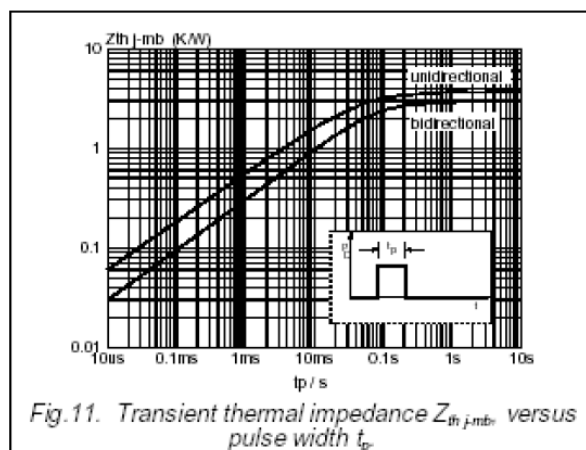
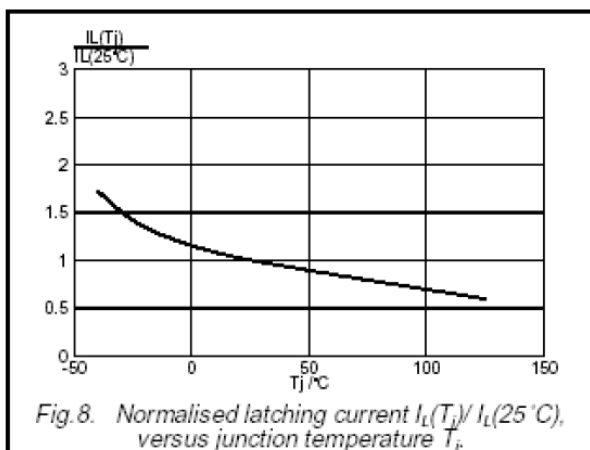
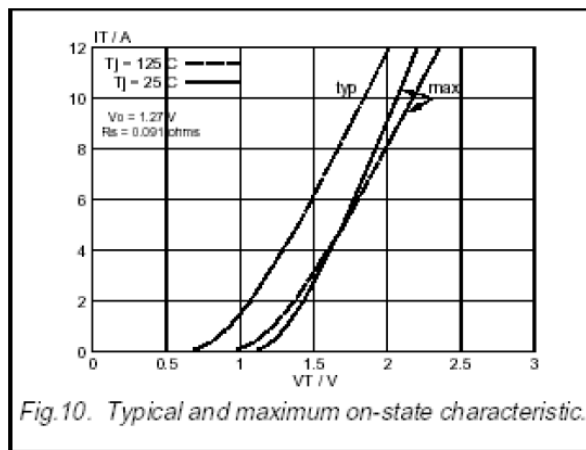
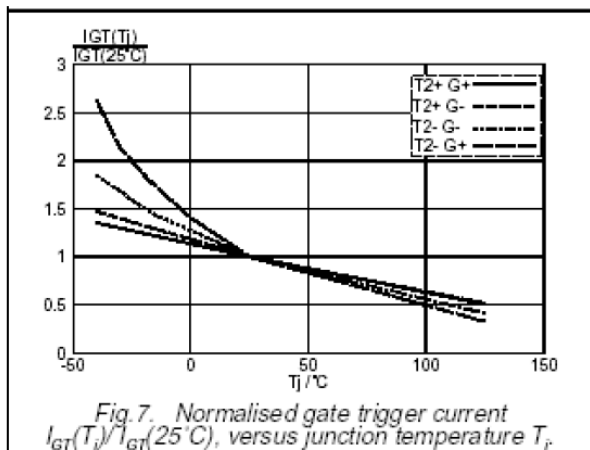


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j) / V_{GT}(25^\circ C)$ , versus junction temperature  $T_j$ .

Note: Specifications are subject to change without notice.

## RATINGS AND CHARACTERISTIC CURVES BT134-600E



Note: Specifications are subject to change without notice.